Ruttonsha International Rectifier Ltd.

RUTTONSHA

SILICON CONTROLLED RECTIFIERS

High Power Thyristor
Hockey Puk Version
E-PUK Series 900PE

Types : 900PE 20 to 900PE 60

900PE...

FEATURES

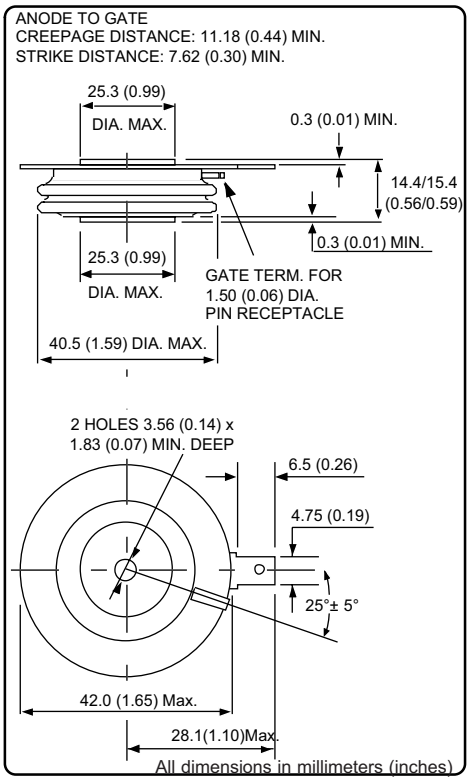
- *Center amplifying gate.*
- *International standard case TO-200AB (E-PUK)*
- *Low profile hockey - puk to increase current carrying capability.*

TYPICAL APPLICATIONS

- *DC motor control (e.g. for machine tools).*
- *Controlled rectifiers (e.g. for battery charging, UPS).*
- *AC controllers (e.g. for temperature control, lights control).*

MAJOR RATINGS & CHARACTERISTICS

Parameters		900PE	Units
$I_{T(AV)}$		960	A
	@ T_{hs}	55	°C
$I_{T(RMS)}$		1900	A
	@ T_{hs}	25	°C
I_{TSM}	@ 50 Hz	15000	A
I^2t	@ 50 Hz	1130	KA^2s
V_{DRM}/V_{RRM}		200 to 600	V
t_q	typical	100	µs
T_J		-40 to 125	°C



SILICON CONTROLLED RECTIFIERS

900PE

ELECTRICAL SPECIFICATION

VOLTAGE RATINGS

Type Number	Voltage Code	V_{RRM} / V_{DRM} max. repetitive peak and off-state voltage V	V_{RSM} max. non-repetitive peak voltage V	I_{DRM} / I_{RRM} max. @ 125°C mA
900PE	20	200	300	50
	40	400	500	
	60	600	700	

ON-STATE CONDUCTION

	Parameter	900PE	Units	Conditions		
$I_{T(AV)}$	Max. average on-state current	960(440)	A	180° conduction, half sine wave		
	@ heat sink temperature	55(75)	°C	double side (single side) cooled		
$I_{T(RMS)}$	Max. RMS on-state current	1900	A	@ 25°C heat sink temperature (double side cooled)		
I_{TSM}	Max. peak one cycle non-repetitive surge current	15000		t = 10ms	No voltage reapplied	Sinusodial half wave, Initial $T_J = T_J$ max.
		12600		t = 10ms	100% V_{RRM} reapplied	
I^2t	Maximum I^2t for fusing	1130	kA^2s	t = 10ms	No voltage reapplied	
		800		t = 10ms	100% V_{RRM} reapplied	
I^2t	Maximum I^2t for fusing	11300	kA^2s	t = 0.1 to 10ms. No voltage reapplied.		
$V_{T(TO)1}$	Low level value of threshold voltage	0.85	V	(16.7% x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ max.		
$V_{T(TO)2}$	High level value of threshold voltage	0.88		(π x $I_{F(AV)}$ < I < 20 x π x $I_{F(AV)}$), $T_J = T_J$ max.		
r_{t1}	Low level value of on state slope resistance	0.25	mΩ	(16.7% x π x $I_{F(AV)}$ < I < π x $I_{F(AV)}$), $T_J = T_J$ max.		
r_{t2}	High level value of on state slope resistance	0.24		(π x $I_{F(AV)}$ < I < 20 x π x $I_{F(AV)}$) $T_J = T_J$ max.		
V_{TM}	Max. on state voltage	1.60	V	I_{pk} = 3000A, T_J = 125°C, t_p = 10ms sine pulse		
I_H	Maximum holding current	600	mA	T_J = 25°C, anode supply 12V resistive load		
I_L	Latching current	1000				

SWITCHING

	Parameter	900PE	Units	Conditions
di/dt	Max. non-repetitive rate of rise of turned-on current	1000	A/µs	Gate drive 20V, 20Ω, tr ≤ 1 µs T_J = 125°C, anode voltage ≤ 80% V_{DRM}
t_d	Typical delay time	1.0	µs	Gate current 1A, di_g/dt = 1A/µs V_d = 0.67% V_{DRM}, T_J = 25°C
t_q	Typical turn-off time	100		I_{TM} = 550A, T_J = 125°C, di/dt = 40A/µs, V_R = 50V dv/dt = 20V/µs, Gate 0V 100Ω, t_p = 500µs

SILICON CONTROLLED RECTIFIERS

900PE

BLOCKING

	Parameter	900PE	Units	Conditions
dv/dt	Maximum critical rate of rise of off-state voltage	1000	V/µs	T_J = 125°C, linear to 80% rated V_{DRM}
I_{RRM} I_{DRM}	Max. peak reverse and off-state leakage current	50	mA	T_J = 125°C, rated V_{DRM}/V_{RRM} applied

TRIGGERING

	Parameter	900PE		Units	Conditions	
P_{GM}	Maximum peak gate power	10.0		W	T_J = 125°C, $t_p \leq$ 5ms	
$P_{G(AV)}$	Maximum average gate power	2.0			T_J = 125°C, f= 50Hz, d% = 50	
I_{GM}	Max. peak positive gate current	3.0		A	T_J = 125°C, $t_p \leq$ 5ms	
$+V_{GM}$	Max. peak positive gate voltage	20		V	T_J = 125°C, $t_p \leq$ 5ms	
$-V_{GM}$	Max. peak negative gate voltage	5.0				
I_{GT}	DC gate current required to trigger	TYP.	MAX.	mA		Max. required gate trigger/current /voltage are the lowest value which will trigger all units 12V anode-to-cathode applied.
		200	--		T_J = -40°C	
		100	200		T_J = 25°C	
		50	--		T_J = 125°C	
V_{GT}	DC gate voltage required to trigger	2.5	--	V	T_J = -40°C	
		1.8	3.0		T_J = 25°C	
		1.1	--		T_J = 125°C	
I_{GD}	DC gate current not to trigger	10		mA	T_J = 125°C	Max. gate current /voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied.
V_{GD}	DC gate voltage not to trigger	0.25		V		

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	900PE	Units	Conditions
T_J	Max. operating temperature range	-40 to 125	°C	
T_{stg}	Max. storage temperature range	-40 to 150		
R_{thJ-hs}	Max. thermal resistance, junction to heat sink	0.09	K/W	DC operation single side cooled
		0.04		DC operation double side cooled
F	Mounting force, ±10%	9800	N	
wt	Approximate weight	83	g	
	Case style	To - 200AB (E-PUK)		See outline

900 PE

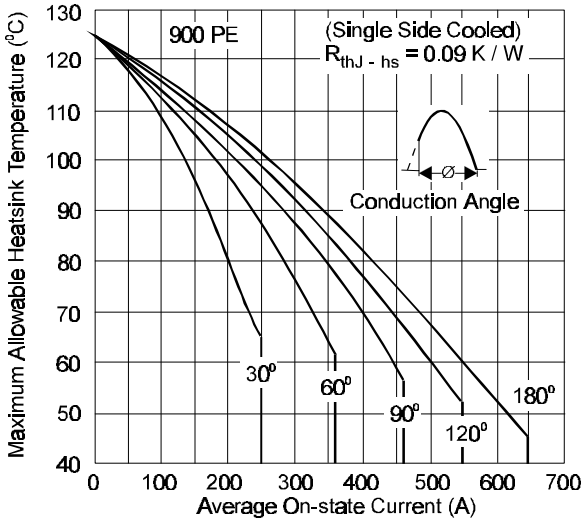


Fig. 1 - Current Ratings Characteristics

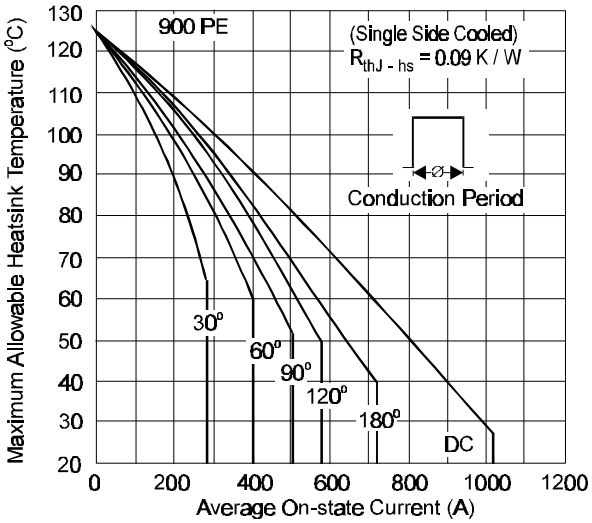


Fig. 2 - Current Ratings Characteristics

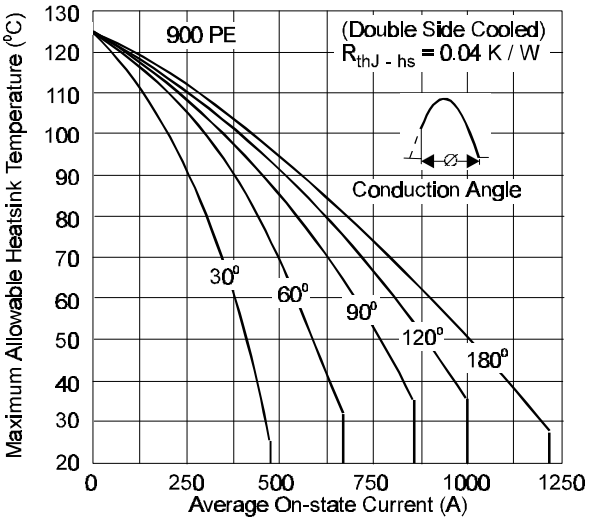


Fig. 3 - Current Ratings Characteristics

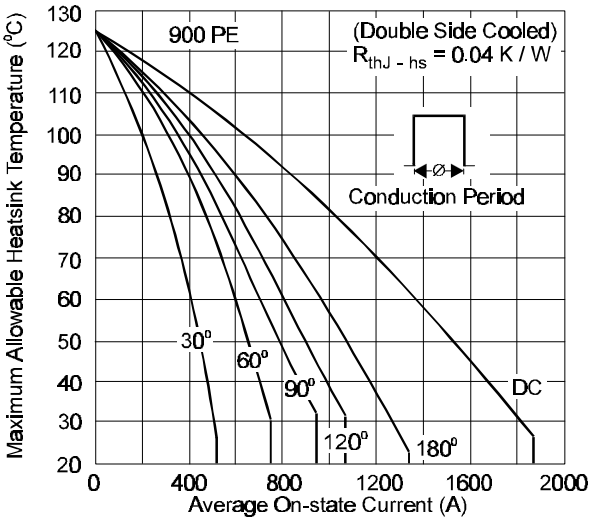


Fig. 4 - Current Ratings Characteristics

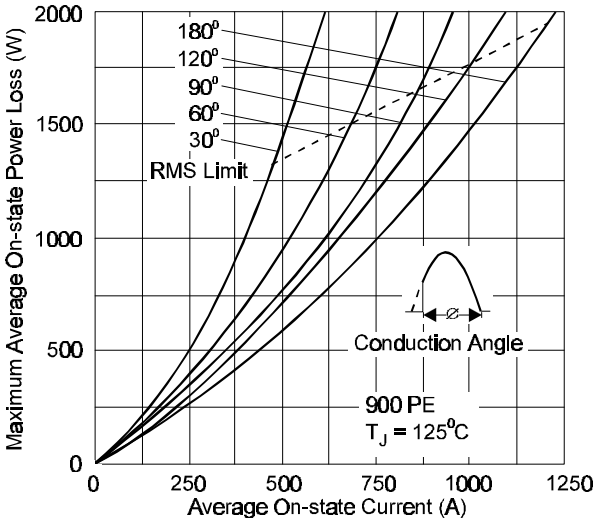


Fig. 5 - On-state Power Loss Characteristics

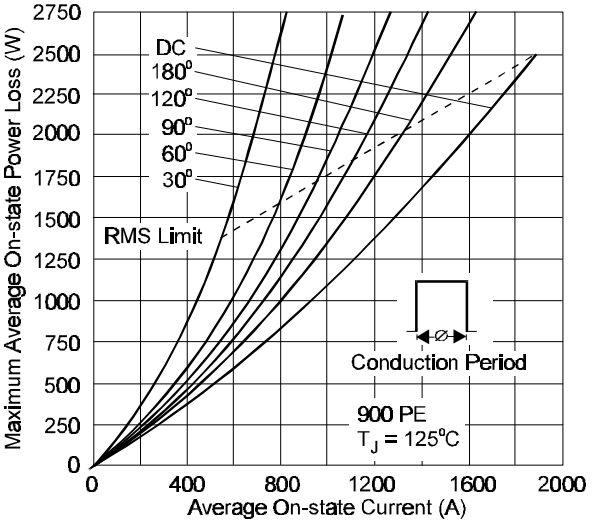


Fig. 6 - On-state Power Loss Characteristics

900 PE

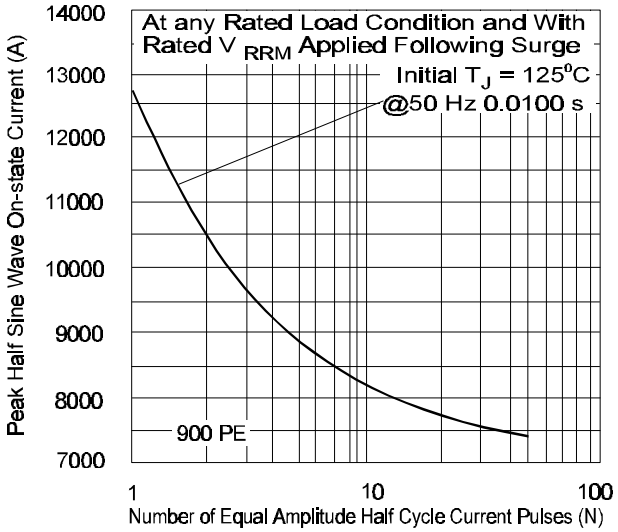


Fig. 7 - Maximum Non-Repetitive Surge Current

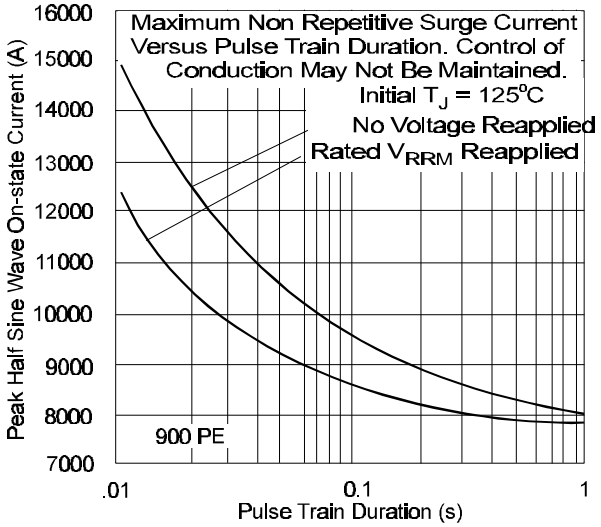


Fig. 8 - Maximum Non-Repetitive Surge Current

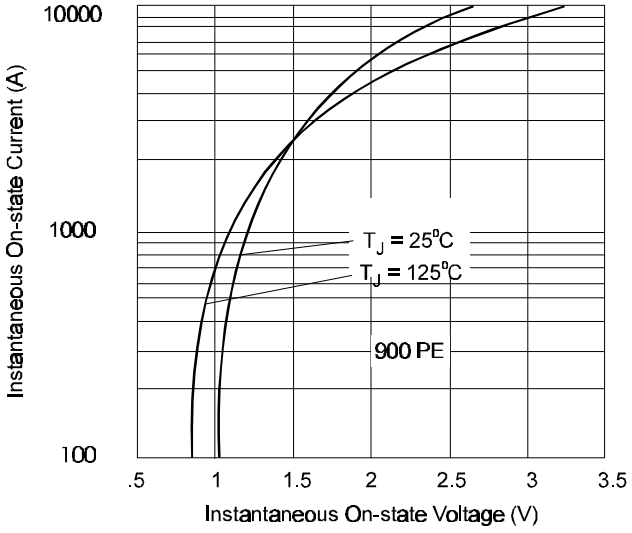


Fig. 9 - On-state Voltage Drop Characteristics

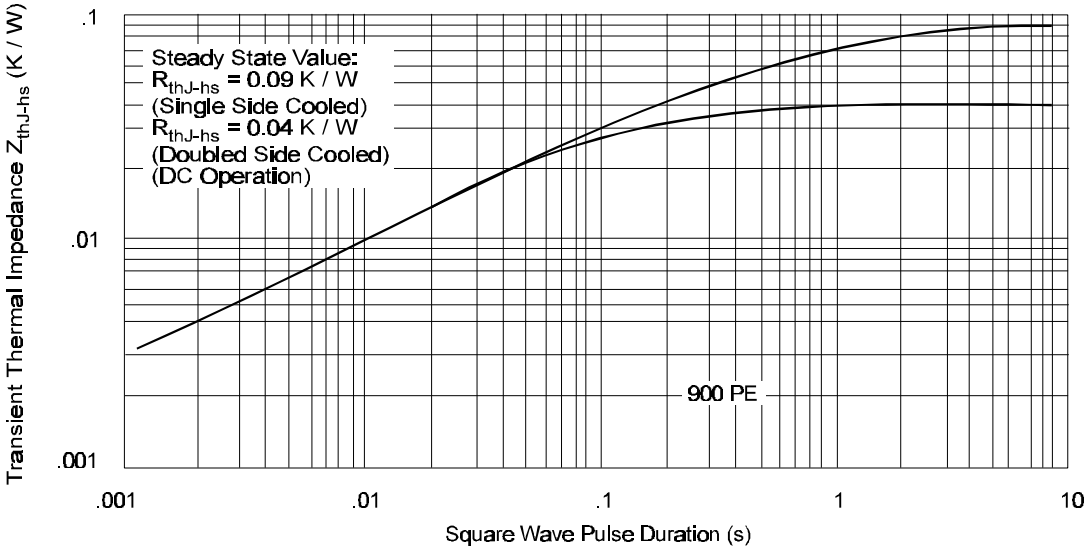


Fig. 10 - Thermal Impedance $Z_{thJ\text{-}hs}$ Characteristics

900 PE

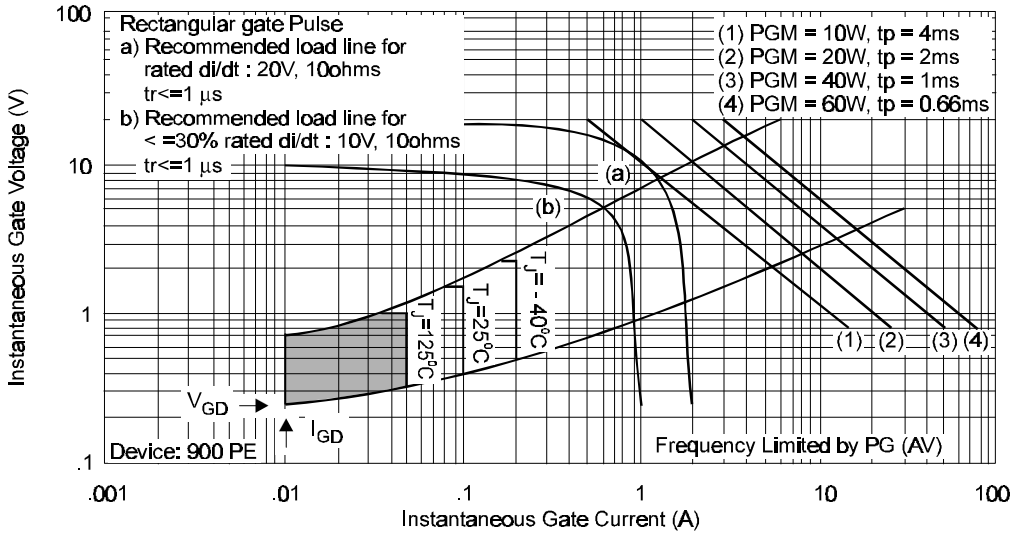


Fig.11 - Gate Characteristics

Last Update : Mar. 2006